

BYV54HR

Aerospace 40 A - 200 V fast recovery rectifier

Features

- Very small conduction losses
- Negligible switching losses
- High surge current capability
- High avalanche energy capability
- Hermetic package
- Target radiation qualification:
 - 150 krad (Si) low dose rate
 - 1 Mrad high dose rate
- Package mass: 10 g
- ESCC qualified

Description

Packaged in a hermetic TO-254AA, this device is intended for use in medium voltage, high frequency switching mode power supplies, high frequency DC to DC converters, and other aerospace applications.

The complete ESCC specification for this device is available from the European space agency web site. ST guarantees full compliance of qualified parts with such ESCC detailed specifications.

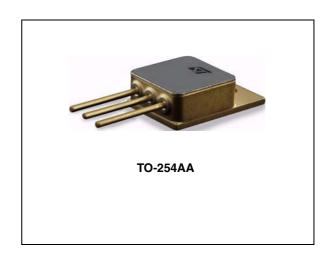


Figure 1. Device configuration

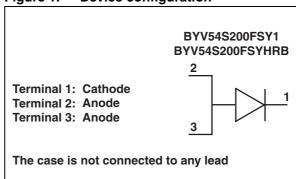


Table 1. Device summary⁽¹⁾

Order code	ESCC detailed specification	Quality level	Lead finish	EPPL	I _{F(AV)}	V _{RRM}	T _{j(max)}	V _{F(max)}
BYV54S200FSY1	-	Engineering model	Gold	-	40 A	200 V	150 °C	1.10 V
BYV54S200FSYHRB	5103/031/05	Flight part	Solder dip	Υ	40 A	200 V	130 0	1.10 V

^{1.} Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.

July 2010 Doc ID 17416 Rev 1 1/8

Characteristics BYV54HR

1 Characteristics

Table 2. Absolute maximum ratings

Symbol	Characteristic	Value	Unit
I _{FSM}	Forward surge current ⁽¹⁾	400	Α
V_{RRM}	Repetitive peak reverse voltage ⁽²⁾	200	V
Io	Average output rectified current (50% duty cycle):(3)	40	Α
I _{F(RMS)}	Forward rms current	60	А
T _{OP}	Operating case temperature range ⁽⁴⁾	-55 to +150	°C
T _J	Junction temperature	+150	°C
T _{STG}	Storage temperature range ⁽⁴⁾	-55 to +150	°C
T _{SOL}	Soldering temperature ⁽⁵⁾	+260	°C

- 1. Sinusoidal pulse of 10 ms duration
- 2. Pulsed, duration 5 ms, F = 50 Hz
- 3. For $T_{case} > +99$ °C, derate linearly to 0 A at +150°C.
- 4. For devices with hot solder dip lead finish all testing performed at $T_{amb} > +125$ °C are carried out in a 100% inert atmosphere.
- 5. Duration 10 seconds maximum at a distance of not less than 1.5 mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case ⁽¹⁾	1.0	°C/W	

1. Package mounted on infinite heatsink.

BYV54HR Characteristics

Table 4. Electrical measurements at ambiant temperature (per diode), $T_{amb} = 22 \pm 3$ °C

Cumbal	Characteristic	MIL-STD-750	Test conditions ⁽¹⁾	Limits		Units
Symbol	Cilaracteristic	test method	rest conditions.	Min.	Max.	Ointo
I _R	Reverse current	4016	DC method, V _R = 200 V	-	50	μΑ
V _{F1} ⁽²⁾	Forward voltage	4011	Pulse method, I _F = 20 A	-	0.95	V
V _{F2} ⁽²⁾	Forward vollage	4011	Pulse method, I _F = 30 A	-	1.1	٧
V_{BR}	Breakdown voltage	4021	I _R = 100 μA	200	-	٧
С	Capacitance	4001	V _R = 10 V, F = 1 MHz	-	400	pF
t _{rr}	Reverse recovery time	4031	$I_F = 1 \text{ A}, V_R = 30 \text{ V},$ $dI_F/dt = -50 \text{ A/}\mu\text{s}$	-	60	ns
Z _{th(j-c)} ⁽³⁾	Relative thermal impedance, junction to case	3101	$I_H = 15 \text{ to } 40 \text{ A}, t_H = 50 \text{ ms}$ $I_M = 50 \text{ mA}, t_{md} = 100 \mu\text{s}$	Calculat	e ΔV _F ⁽⁴⁾	°C/W

- 1. Testing performed with both anode terminals 2 and 3 tied ttogehter
- 2. Pulse width \leq 680 μ s, duty cycle \leq 2%
- 3. Performed only during screening tests parameter drift values (initial measurements for HTRB), go-no-go.
- 4. The limits for Δ VF shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the R_{th(j-c)} limits specified in maximum ratings.

Table 5. Electrical measurements at high and low temperatures (per diode)

Cumbal	Characteristic	MIL-STD-750	Test conditions ⁽¹⁾	Limits		Units
Symbol	Characteristic	test method	rest conditions.	Min.	Max.	Oiills
I _R	Reverse current	4016	$T_{case} = +125 (+0, -5) ^{\circ}C$ DC method, $V_{R} = 200 V$	-	40	mA
V _{F1} ⁽²⁾		$T_{case} = +125 (+0, -5) ^{\circ}C$ pulse method, $I_F = 20 \text{ A}$ $T_{case} = -55 (+0, -5) ^{\circ}C$ pulse method, $I_F = 20 \text{ A}$	-	0.85	V	
	Forward voltage			-	1.15	V
V _{F2} ⁽²⁾			T_{case} = +125 (+0, -5) °C pulse method, I_F = 30 A		1.0	

^{1.} Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

To evaluate the conduction losses use the following equation:

$$P = 0.74 \times I_{F(AV)} + 1.00 \times I_{F}^{2}(RMS)$$

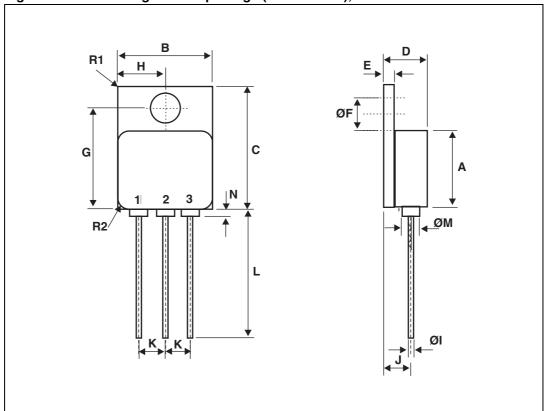
^{2.} Pulse width $\leq 680~\mu s,~duty~cycle \leq 2\%$

Package information BYV54HR

Package information 2

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Metal flange mount package (TO-254AA^(a)), 3 lead dimension definitions Figure 2.



4/8

a. The terminal identification is specified by the device configuration. See Figure 1 for terminal connections

Table 6. Metal flange mount package (TO-254), 3-lead dimension values

Deference	Dimension in	n millimetres	Dimlension	n in inches	
Reference	Min.	Max.	Min.	Max.	
А	13.59	13.84	0.535	0.545	
В	13.59	13.84	0.535	0.545	
С	20.07	20.32	0.790	0.800	
D	6.3	6.7	0.248	0.264	
E	1	3.9	0.039	0.154	
ØF	3.5	3.9	0.138	0.154	
G	16.89	17.4	0.665	0.685	
Н	6.86	BSC	0.270 BSC		
ØI ⁽¹⁾	0.89	1.14	0.035	0.045	
J	3.81	BSC	0.150 BSC		
K	3.81	BSC	0.150 BSC		
L	12.95	14.5	0.510	0.571	
ØM	3.05	3.05 Typ.		Тур.	
N	-	0.71	-	0.028	
R1 ⁽²⁾	-	1	-	0.039	
R2 ⁽³⁾	1.65 Typ.		0.0	065	

^{1. 3} locations

^{2.} Radius of heatsink flange corner - 4 locations

^{3.} Radius of body corner - 4 locations

3 Ordering information

Table 7. Ordering information⁽¹⁾

Order code	ESCC detailed specification	Package	Lead finish	Comment	Marking	Mass	EPPL	Packing
BYV54S200FSY1	-	TO-254AA	Gold	Single die	BYV54S200FSY1 + BeO	10 a	-	Strip
BYV54S200FSYHRB	5103/031/05	10-254AA	Solder dip	Sirigle die	510303105 + BeO	10 g	Υ	pack

^{1.} Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.

BYV54HR Revision history

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
08-Jul-2010	1	First issue.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

